

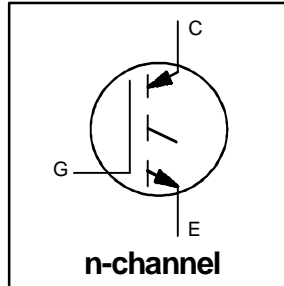
IRGBC40M

INSULATED GATE BIPOLAR TRANSISTOR

Short Circuit Rated
Fast IGBT

Features

- Short circuit rated - 10 μ s @ 125°C, $V_{GE} = 15V$
- Switching-loss rating includes all "tail" losses
- Optimized for medium operating frequency (1 to 10kHz)

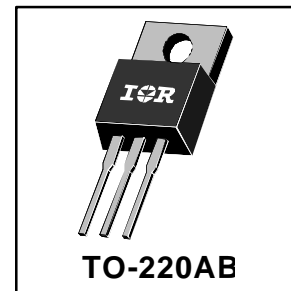


$V_{CES} = 600V$
$V_{CE(sat)} \leq 3.0V$
@ $V_{GE} = 15V, I_C = 24A$

Description

Insulated Gate Bipolar Transistors (IGBTs) from International Rectifier have higher usable current densities than comparable bipolar transistors, while at the same time having simpler gate-drive requirements of the familiar power MOSFET. They provide substantial benefits to a host of high-voltage, high-current applications.

These new short circuit rated devices are especially suited for motor control and other applications requiring short circuit withstand capability.



Absolute Maximum Ratings

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Voltage	600	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	40	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	24	
I_{CM}	Pulsed Collector Current ①	80	
I_{LM}	Clamped Inductive Load Current ②	80	
t_{sc}	Short Circuit Withstand Time	10	μ s
V_{GE}	Gate-to-Emitter Voltage	± 20	V
E_{ARV}	Reverse Voltage Avalanche Energy ③	15	mJ
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	160	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	65	
T_J	Operating Junction and Storage Temperature Range	-55 to +150	$^\circ C$
T_{STG}			
	Mounting torque, 6-32 or M3 screw.	10 lbf•in (1.1N•m)	

Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	—	0.77	$^\circ C/W$
$R_{\theta CS}$	Case-to-Sink, flat, greased surface	—	0.50	—	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount	—	—	80	
Wt	Weight	—	2 (0.07)	—	g (oz)

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions	
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage	600	—	—	V	$V_{GE} = 0V, I_C = 250\mu A$	
$V_{(BR)ECS}$	Emitter-to-Collector Breakdown Voltage ④	20	—	—	V	$V_{GE} = 0V, I_C = 1.0A$	
$\Delta V_{(BR)CES}/\Delta T_J$	Temp. Coeff. of Breakdown Voltage	—	0.70	—	V/°C	$V_{GE} = 0V, I_C = 1.0mA$	
$V_{CE(on)}$	Collector-to-Emitter Saturation Voltage	—	2.0	3.0	V	$I_C = 24A, V_{GE} = 15V$	
		—	2.6	—			$I_C = 40A$
		—	2.4	—			$I_C = 24A, T_J = 150^\circ\text{C}$
$V_{GE(th)}$	Gate Threshold Voltage	3.0	—	5.5		$V_{CE} = V_{GE}, I_C = 250\mu A$	
$\Delta V_{GE(th)}/\Delta T_J$	Temperature Coeff. of Threshold Voltage	—	-12	—	mV/°C	$V_{CE} = V_{GE}, I_C = 250\mu A$	
g_{fe}	Forward Transconductance ③	9.2	12	—	S	$V_{CE} = 100V, I_C = 24A$	
I_{CES}	Zero Gate Voltage Collector Current	—	—	250	μA	$V_{GE} = 0V, V_{CE} = 600V$	
		—	—	1000		$V_{GE} = 0V, V_{CE} = 600V, T_J = 150^\circ\text{C}$	
I_{GES}	Gate-to-Emitter Leakage Current	—	—	± 100	nA	$V_{GE} = \pm 20V$	

Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions	
Q_g	Total Gate Charge (turn-on)	—	59	80	nC	$I_C = 24A$ $V_{CC} = 400V$ $V_{GE} = 15V$	
Q_{ge}	Gate - Emitter Charge (turn-on)	—	8.6	10			
Q_{gc}	Gate - Collector Charge (turn-on)	—	25	42			
$t_{d(on)}$	Turn-On Delay Time	—	26	—	ns	$T_J = 25^\circ\text{C}$ $I_C = 24A, V_{CC} = 480V$ $V_{GE} = 15V, R_G = 10\Omega$ Energy losses include "tail"	
t_r	Rise Time	—	37	—			
$t_{d(off)}$	Turn-Off Delay Time	—	240	410			
t_f	Fall Time	—	230	420			
E_{on}	Turn-On Switching Loss	—	0.75	—			mJ
E_{off}	Turn-Off Switching Loss	—	1.65	—			
E_{ts}	Total Switching Loss	—	2.4	3.6			
t_{sc}	Short Circuit Withstand Time	10	—	—	μs	$V_{CC} = 360V, T_J = 125^\circ\text{C}$ $V_{GE} = 15V, R_G = 10\Omega, V_{CPK} < 500V$	
$t_{d(on)}$	Turn-On Delay Time	—	28	—	ns	$T_J = 150^\circ\text{C}$, $I_C = 24A, V_{CC} = 480V$ $V_{GE} = 15V, R_G = 10\Omega$ Energy losses include "tail"	
t_r	Rise Time	—	37	—			
$t_{d(off)}$	Turn-Off Delay Time	—	380	—			
t_f	Fall Time	—	460	—			
E_{ts}	Total Switching Loss	—	4.5	—	mJ		
L_E	Internal Emitter Inductance	—	7.5	—	nH	Measured 5mm from package	
C_{ies}	Input Capacitance	—	1500	—	pF	$V_{GE} = 0V$ $V_{CC} = 30V$ $f = 1.0MHz$	
C_{oes}	Output Capacitance	—	190	—			
C_{res}	Reverse Transfer Capacitance	—	20	—			

- Notes:**
- ① Repetitive rating; $V_{GE}=20V$, pulse width limited by max. junction temperature.
 - ② $V_{CC}=80\%(V_{CES}), V_{GE}=20V, L=10\mu H, R_G=10\Omega$
 - ③ Repetitive rating; pulse width limited by maximum junction temperature.
 - ④ Pulse width $\leq 80\mu s$; duty factor $\leq 0.1\%$.
 - ⑤ Pulse width 5.0 μs , single shot.

Refer to Section D for the following:

Package Outline 1 - JEDEC Outline TO-220AB

Section D - page D-12

Note: For the most current drawings please refer to the IR website at:
<http://www.irf.com/package/>